

/ Descriptions

TO-252 N MOS N-CHANNEL MOSFET in a TO-252 Plastic Package.

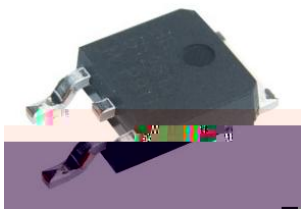
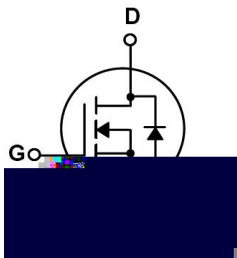
/ Features

DS dv/dt
Low $R_{DS(ON)}$, Low gate charge, Low C_{rss} , Fast switching, Improved dv/dt capability.

/ Applications 4

DC/DC

These devices are well suited for high efficiency switching DC/DC converters and switch mode power supplies.



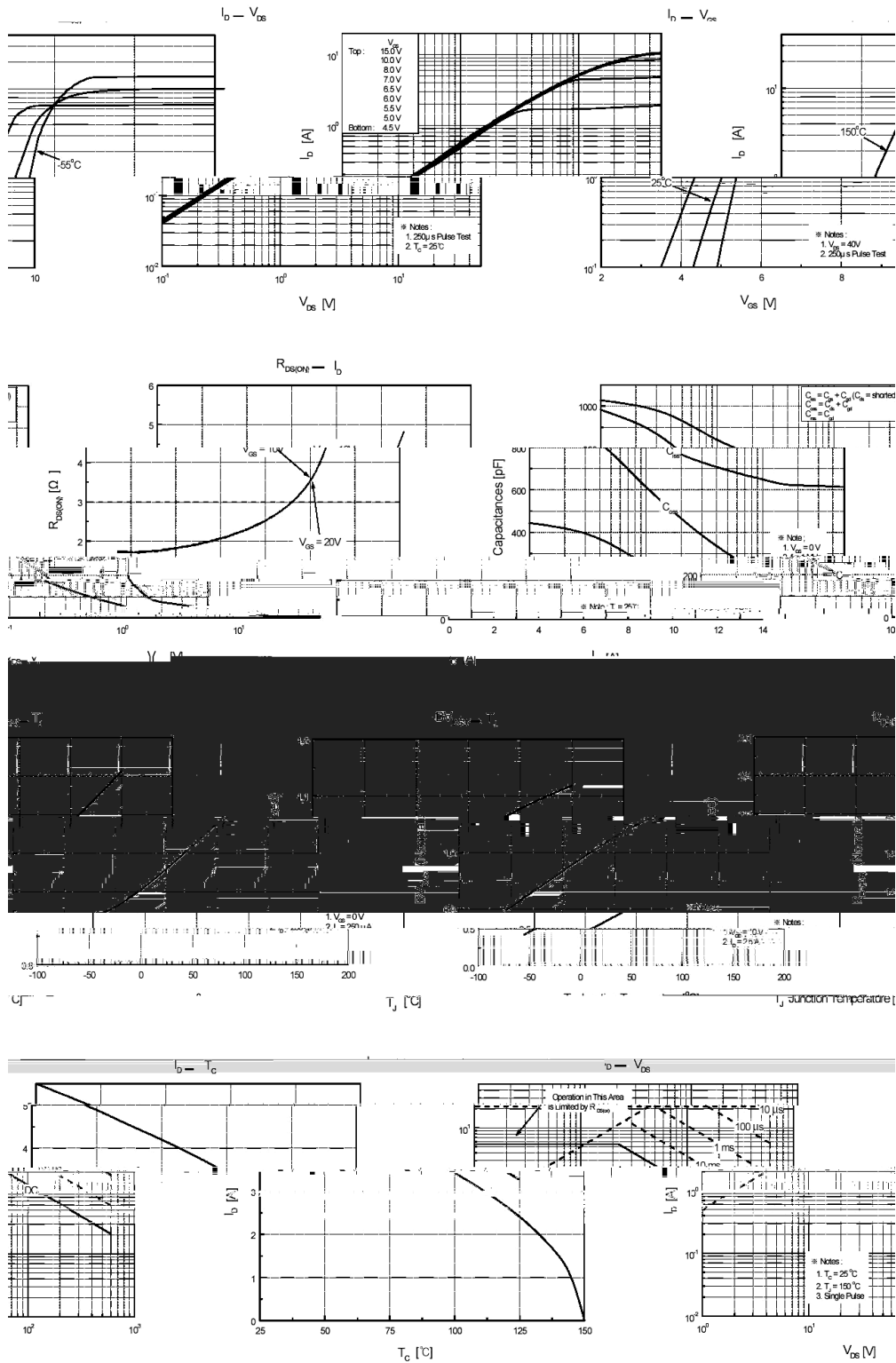
PIN1 G PIN 2 D PIN 3 S PIN 4 D

/ h_{FE} Classifications & Marking

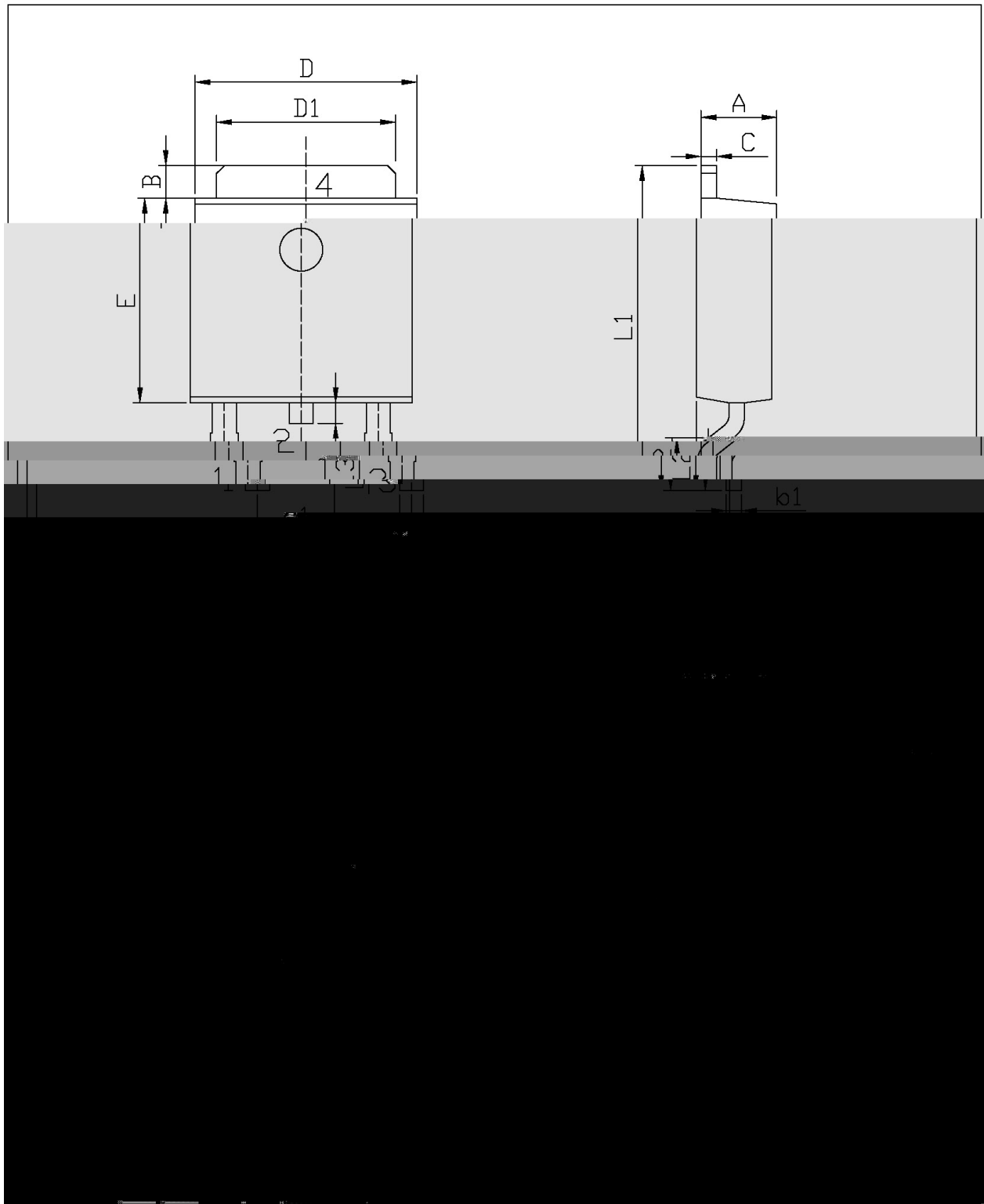
See Marking Instructions.

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	600	V
Drain Current	$I_D(T_c=25^{\circ}\text{C})$	5.5	A
Drain Current	$I_D(T_c=100^{\circ}\text{C})$	3.3	A
Drain Current - Pulsed	I_{DM}	22	A
Gate-Source Voltage	V_{GS}	± 30	V
Single Pulsed Avalanche Energy	E_{AS}	300	mJ
Repetitive Avalanche Energy	E_{AR}	12.5	mJ
Avalanche Current	I_{AR}	5.5	A
Power Dissipation	$P_D(T_c=25^{\circ}\text{C})$	40	W
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to 150	

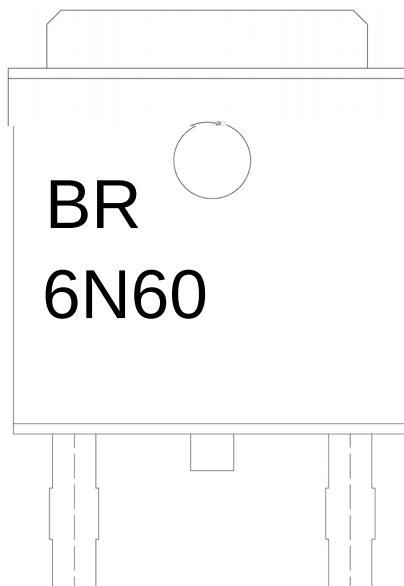
/ Electrical Characteristic Curve



/ Package Dimensions



/ Marking Instructions



BR

6N60

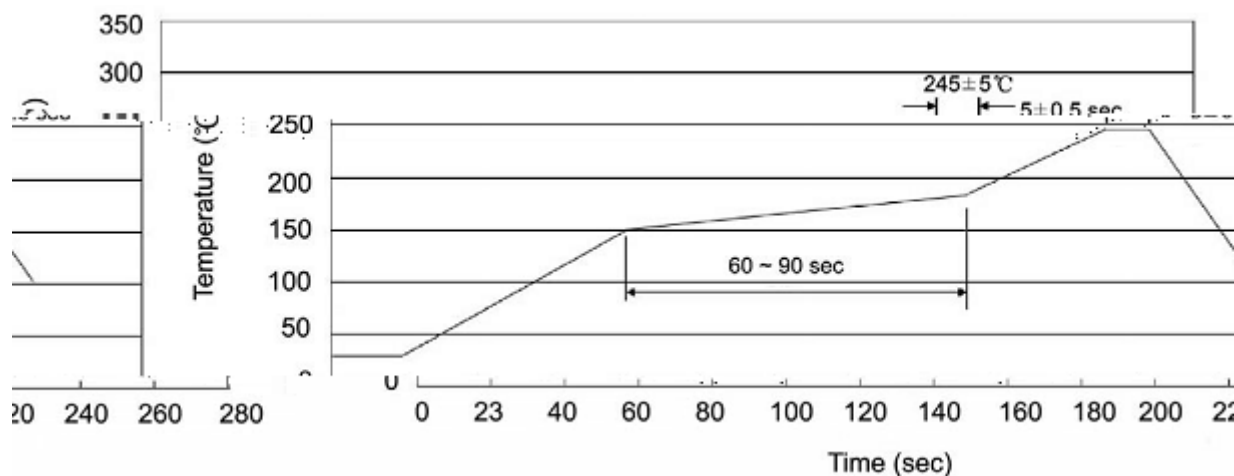
Note:

BR: Company Code

6N60: Product Type.

****: Lot No. Code, code change with Lot No.

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Note:

- | | | | | | |
|---|-------|-----|-----------|--------|---|
| 1 | 25 | 150 | 60 | 90sec; | 1.Preheating:25~150 , Time:60~90sec. |
| 2 | 245±5 | | 5±0.5sec; | | 2.Peak Temp.:245±5 , Duration:5±0.5sec. |
| 3 | | 2 | 10 | /sec. | 3. Cooling Speed: 2~10 /sec. |

/ Resistance to Soldering Heat Test Conditions

260±5 10±1 sec. Temp.:260±5 Time:10±1 sec

/ Packaging SPEC.

/ REEL

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)		
	只 卷盘	卷盘 盒	只 盒	盒 箱	只 箱		盒	箱
						"		

/ TUBE

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)		
	只 套管	套管 盒	只 盒	盒 箱	只 箱	套管	盒	箱

/ Notices